



UNIVERSITÀ
degli STUDI
di CATANIA

DIPARTIMENTO DI FISICA E ASTRONOMIA
“ETTORE MAJORANA”

DOTTORATO DI RICERCA IN FISICA

CICLO XXXVI
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Charge transport and devices simulation

2 CFU

Teaching staff

ANTONINO LA MAGNA

Email: Antonino.LaMagna@imm.cnr.it

Office: Zona Industriale VIII Strada 5 I 95121 Catania Italy

Telephone: +39 095 5868220

Reception hours: Friday 11:00-13:00

Program of the course:

Introduction to the quantum and semiclassical charge transport: Ohm law - From semiclassical/continuum to quantum/atomistic formalisms - Contact resistance concept - Landauer formula - bottom-up: one level device.

Quantitative numerical analysis of the quantum carrier dynamics: Charging and self-consistency - Quantum capacitance - Coulomb blockade - Non Equilibrium Green Function - Contact Self Energies- el-ph scattering - perturbative corrections - variational formalism - examples: graphene, nanotubes, atoms' chains.

Boltzmann formalism and semiclassical methods: semiclassical carriers - Boltzmann equation - Scattering kernels - Fermi Golden rule - relaxation times - Phonon scattering - Impurity scattering - charge/charge scattering - Avalanche carriers' generation - Monte Carlo approach - Monte Carlo - Poisson Device simulation - Continuum models - Drift Diffusion models and device simulations - Hydrodynamic models and device simulation - TCAD introduction.

Bibliography:

- S.M. Sze. K. K. Ng “Physics of Semiconductor Devices John Wiley & Sons, Inc.”
- K.Tomizawa “Numerical Simulation of Submicron Semiconductor devices” Artech House Inc. Norwood
- S. Datta “Quantum Transport: Atom to Transistor” Cambridge University Press
- S. Datta “Electronic Transport in Mesoscopic Systems” Cambridge University Press